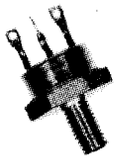


silicon power transistors

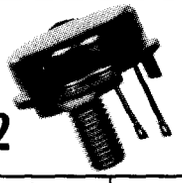
NPN TO-61 (isolated collector) (cont'd)

$I_{C(MAX)}$ = 5 to 20A $V_{CEO(SUS)}$ = 60 to 350V f_T = 20 to 40 MHz

Type #	$V_{CEO(SUS)}$ (Volts)	h_{FE} @ I_C/V_{CE} (Min-Max @ A/V)	$V_{CE(SAT)}$ @ I_C/I_B (V @ A/A)	V_{BE} @ I_C/V_{CE} (V @ A/V)	I_{CEV} @ V_{CE} (mA @ V)	P_D @ T_C =100°C (Watts)	θ_{JC} (°C/W)	$I_{s/b}$ @ V_{CE} t = 1sec (A @ V)	f_T (MHz)	t_{ON} @ I_C/I_B (μs @ A/A)	t_{OFF} @ I_C/I_B (μs @ A/A)	Generic Product	General Information
STA9760	225	10-200@10/4	2@10/1	2.5[3]@10/1	.5@225	57	1.75	2.85@20	20	.6@10/1	3@10/1	STA9760 Family. 200 x 200 Mil Chip. Double Epitaxial Process. Ultrasonicly Bonded Leads. Case 352	High Voltage, High Current, High Speed Power Switch and Amplifier. Military Usage.
STA9761	300	10-200@8/4	2@8/.8	2.5[3]@8/.8	1.0@300	57	1.75	2.85@20	20	.6@8/.8	3@8/.8		
STA 9762	350	10-200@5/4	2@5/.5	2.5[3]@5/.5	1.0@350	57	1.75	2.85@20	20	.5@5/.5	3@5/.5		
Typical Values	275	10-200@5/4	1@5/.5	1.8[3]@5/.5	1@275	57	1.75	2.85@20	20	.5@5/.5	2.5@5/.5		

NOTE: This product is developmental.

NOTES:
[3] $V_{BE(SAT)}$ @ I_C/I_B (V @ A/A)



NPN TO-82

$I_{C(MAX)}$ = 7.5 to 10A $V_{CEO(SUS)}$ = 30 to 250V f_T = 0.5 MHz

Type #	$V_{CEO(SUS)}$ (Volts)	h_{FE} @ I_C/V_{CE} (Min-Max @ A/V)	$V_{CE(SAT)}$ @ I_C/I_B (V @ A/A)	V_{BE} @ I_C/V_{CE} (V @ A/V)	I_{CEV} @ V_{CE} (mA @ V)	P_D @ T_C =100°C (Watts)	θ_{JC} (°C/W)	$I_{s/b}$ @ V_{CE} t = 1sec (A @ V)	f_T (MHz)	t_{ON} @ I_C/I_B (μs @ A/A)	t_{OFF} @ I_C/I_B (μs @ A/A)	Generic Product	General Information
2N1015	30	>10@2/4	1.5@2/.3	2@2/4	20@30	71.5	0.7					2N1016 Family. 200 x 200 Mil Chip. Single Diffused Process. Clip Leads. Case 540	High Power Switch and Amplifier. Military Usage.
2N1015A	60	>10@2/4	1.5@2/.3	2@2/4	20@60	71.5	0.7						
2N1015B	100	>10@2/4	1.5@2/.3	2@2/4	20@100	71.5	0.7						
2N1015C	150	>10@2/4	1.5@2/.3	2@2/4	20@150	71.5	0.7						
2N1015D	200	>10@2/4	1.5@2/.3	2@2/4	20@200	71.5	0.7						
2N1015E	250	>10@2/4	1.5@2/.3	2@2/4	20@250	71.5	0.7						
2N1016	30	>10@5/4	2.5@5/.75	2@5/4	20@30	71.5	0.7						
2N1016A	60	>10@5/4	2.5@5/.75	2@5/4	20@60	71.5	0.7						
2N1016B	100	>10@5/4	2.5@5/.75	2@5/4	20@100	71.5	0.7						
2N1016C	150	>10@5/4	2.5@5/.75	2@5/4	20@150	71.5	0.7						
2N1016D	200	>10@5/4	2.5@5/.75	2@5/4	20@200	71.5	0.7						
2N1016E	250	>10@5/4	2.5@5/.75	2@5/4	20@250	71.5	0.7						
Typical Values	175	10-100@5/4	1.5@5/.75	1.8@5/4	5@175	71.5	0.7	3@50	0.8	6@5/1	13@5/1		
2N2226	50	100-500@9/6	3.5@9/.15	4@9/6	20@50	100	0.5					2N2226 Family. 2 - 170 x 170 Mil Chips in Darlington Configuration. Single Diffused Process. Clip Leads. Case 540	High Gain, High Power Amplifier and Switch. Military Usage.
2N2227	100	100-500@9/6	3.5@9/.15	4@9/6	20@100	100	0.5						
2N2228	150	100-500@9/6	3.5@9/.15	4@9/6	20@150	100	0.5						
2N2229	200	100-500@9/6	3.5@9/.15	4@9/6	20@200	100	0.5						
2N2230	50	>350@8/6	3.5@9/.15	4@9/6	20@50	100	0.5						
2N2231	100	>350@8/6	3.5@9/.15	4@9/6	20@100	100	0.5						
2N2232	150	>350@8/6	3.5@9/.15	4@9/6	20@150	100	0.5						
2N2233	200	>350@8/6	3.5@9/.15	4@9/6	20@200	100	0.5						
Typical Values	100	100-2000@9/6	3@9/.15	3.5@9/6	5@100	100	0.5	3@40	0.8				

NPN TO-63

$I_{C(MAX)}$ = 10 to 30A $V_{CEO(SUS)}$ = 60 to 350V f_T = 0.6 to 30 MHz

Type #	$V_{CEO(SUS)}$ (Volts)	h_{FE} @ I_C/V_{CE} (Min-Max @ A/V)	$V_{CE(SAT)}$ @ I_C/I_B (V @ A/A)	V_{BE} @ I_C/V_{CE} (V @ A/V)	I_{CEV} @ V_{CE} (mA @ V)	P_D @ T_C =100°C (Watts)	θ_{JC} (°C/W)	$I_{s/b}$ @ V_{CE} t = 1sec (A @ V)	f_T (MHz)	t_{ON} @ I_C/I_B (μs @ A/A)	t_{OFF} @ I_C/I_B (μs @ A/A)	Generic Product	General Information
2N2815	80	10-50@10/3	1.5@10/1.5	2.5[3]@10/1.5	2@80	100	1.0		0.6	3.5@10/1.5	12@10/1.5	2N2815 Family. 325 x 325 Mil Chip. Single Diffused Process. Clip Leads. Case 530	Hign Current, High Power Switch and Amplifier. Military Usage.
2N2816	100	10-50@10/3	1.5@10/1.5	2.5[3]@10/1.5	2@100	100	1.0		0.6	3.5@10/1.5	12@10/1.5		
2N2817	150	10-50@10/3	1.5@10/1.5	2.5[3]@10/1.5	2@150	100	1.0		0.6	3.5@10/1.5	12@10/1.5		
2N2818	200	10-50@10/3	1.5@10/1.5	2.5[3]@10/1.5	2@200	100	1.0		0.6	3.5@10/1.5	12@10/1.5		
2N2819	80	10-50@15/3	1.5@15/2.2	2.5[3]@15/2.2	2@80	100	1.0		0.6	3.5@15/2.2	12@15/2.2		
2N2820	100	10-50@15/3	1.5@15/2.2	2.5[3]@15/2.2	2@100	100	1.0		0.6	3.5@15/2.2	12@15/2.2		
2N2821	150	10-50@15/3	1.5@15/2.2	2.5[3]@15/2.2	2@150	100	1.0		0.6	3.5@15/2.2	12@15/2.2		
2N2822	200	10-50@15/3	1.5@15/2.2	2.5[3]@15/2.2	2@200	100	1.0		0.6	3.5@15/2.2	12@15/2.2		
2N2823	80	10-40@20/2	1.1@20/3	2.1[3]@20/3	2@80	100	1.0		0.6	3.5@20/3	12@20/3		
2N2824	100	10-40@20/2	1.1@20/3	2.1[3]@20/3	2@100	100	1.0		0.6	3.5@20/3	12@20/3		
2N2825	150	10-40@20/2	1.1@20/3	2.1[3]@20/3	2@150	100	1.0		0.6	3.5@20/3	12@20/3		
Typical Values	125	10-100@15/3	1.2@15/2.2	1.9[3]@15/2.2	1@125	100	1.0	3@50	0.6	3@15/2.2	10@15/2.2		
STA3265	90	25-55@15/2	1@20/2	1.8[3]@20/2	20@150	100	1.0	.35@75	20	.5@15/1.2	2@15/1.2	STA3265 Family. 200 x 200 Mil Chip. Double Epitaxial Process. Ultrasonicly Bonded Leads. Case 531	High Current, High Speed Power Switch and Amplifier. Military Usage.
STA3266	60	20-80@15/3	1.6@20/2	2.2[3]@20/2	20@120	100	1.0	.70@50	20	.5@15/1.2	2@15/1.2		
STA8860	140	20-200@12/3	1.5@12/1.2	1.8[3]@12/1.2	5@140	100	1.0		30	.5@12/1.2	1@12/1.2		
Typical Values	120	20-200@12/3	.8@12/1.2	1.5[3]@12/1.2	1@120	100	1.0	.7@50	30	.4@12/1.2	1@12/1.2		

NOTE: This product is developmental.

[3] $V_{BE(SAT)}$ @ I_C/I_B (V @ A/A)